

ABSTRACT

When a semiconductor light emitting device or a semiconductor device is manufactured by growing 5 nitride III-V compound semiconductor layers, which will form a light emitting device structure or a device structure, on a nitride III-V compound semiconductor substrate composed of a first region in form of a crystal having a first average dislocation density and 10 a plurality of second regions having a second average dislocation density higher than the first average dislocation density and periodically aligned in the first region, device regions are defined on the nitride III-V compound semiconductor substrate such that the 15 device regions do not substantially include second regions, emission regions or active regions of devices finally obtained do not include second regions.